Docket No.: 09852/0205523-US0

LISTING OF THE CLAIM

1. (Original) A silicon electrode plate for plasma etching with superior durability, the silicon electrode plate comprising silicon single crystal which, in terms of atomic ratio, contains 3 to 11 ppba of boron, and further contains a total of 0.5 to 6 ppba of either or both of phosphorus and arsenic.